Micro Commercial Components
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1N914(A)(B)

500mW 100 Volt Silicon Epitaxial Diodes

Features

- Low Current Leakage
- Compression Bond Construction
- Low Cost

Maximum Ratings

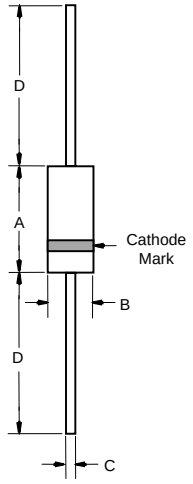
- Operating Temperature: -55°C to +150°C
- Storage Temperature: -55°C to +150°C
- Maximum Thermal Resistance; 300°C/W Junction To Ambient

Electrical Characteristics @ 25°C Unless Otherwise Specified

Maximum Repetitive Reverse Voltage	V_{RRM}	100V	
Average Rectified Forward Current	I_O	200mA	
Power Dissipation	P_D	500mW	
Junction Temperature	T_J	150°C	
Peak Forward Surge Current	I_{FSM}	1.0A 4.0A	Pulse Width=1.0 second Pulse Width=1.0 microsecond
Minimum Breakdown Voltage	V_R	100V 75V	I_R=100uA, I_R=5.0uA
Maximum Instantaneous Forward Voltage 1N914 1N914 A 1N914 B 1N914 B	V_F	1.0V 720mV	T_J = 25°C I_{FM} = 10mA; I_{FM} = 20mA; I_{FM} = 100mA; I_{FM} = 5.0mA;
Maximum Reverse Current	I_R	25nA 5.0uA 50uA	V_R=20V, T_J=25°C, V_R=75V, T_J=25°C, V_R=20V, T_J=150°C
Typical Junction Capacitance	C_J	4.0pF	Measured at 1.0MHz, V_R=0V
Reverse Recovery Time	T_{rr}	4.0nS	I_F=10mA V_R = 6V R_L=100 Ù, I_{rr}=1.0mA

*Pulse test: Pulse width 300 usec, Duty cycle 2%

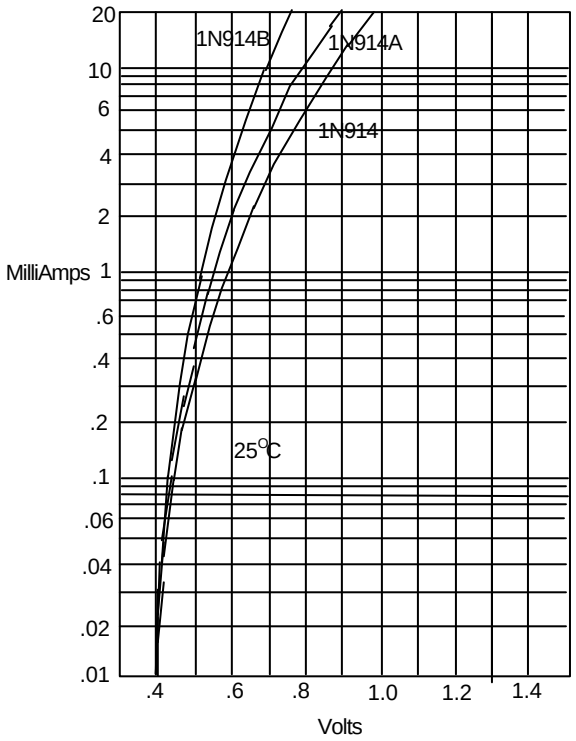
DO-35



DIMENSIONS					
	INCHES		MM		
DIM	MIN	MAX	MIN	MAX	NOTE
A	---	.166	---	4.2	
B	---	.079	---	2.00	
C	---	.020	---	.52	
D	1.000	---	25.40	---	

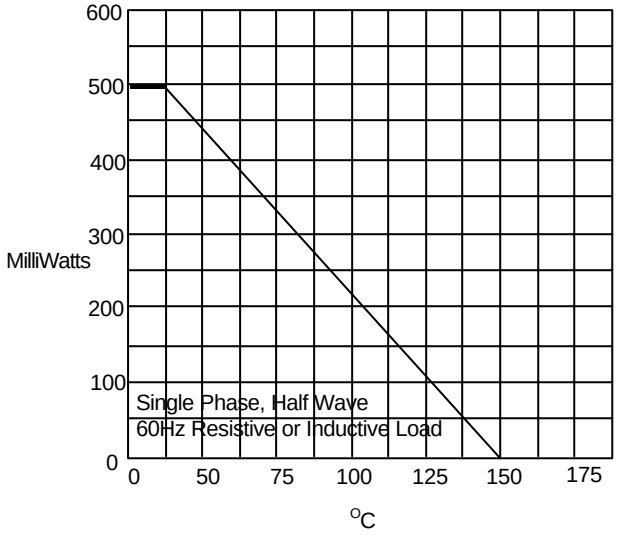
1N914(A)(B)

Figure 1
Typical Forward Characteristics



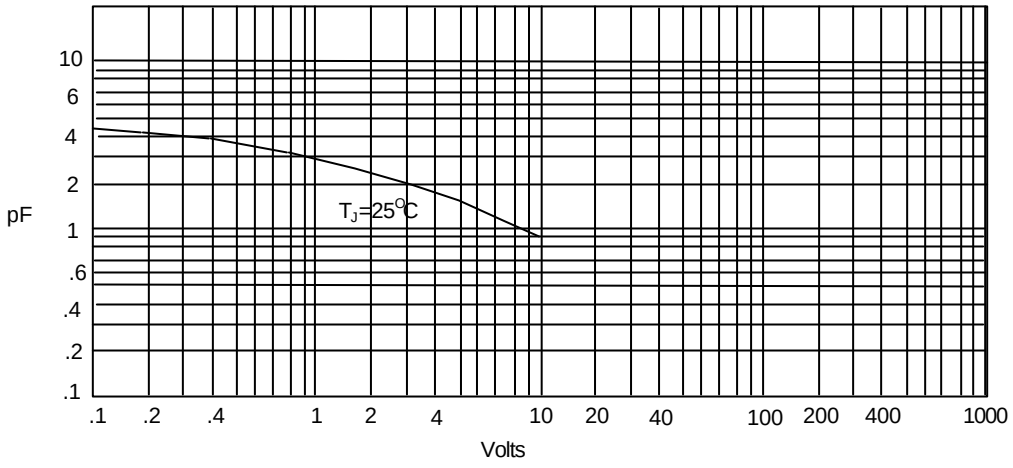
Instantaneous Forward Current - Amperes *versus*
Instantaneous Forward Voltage - Volts

Figure 2
Forward De rating Curve



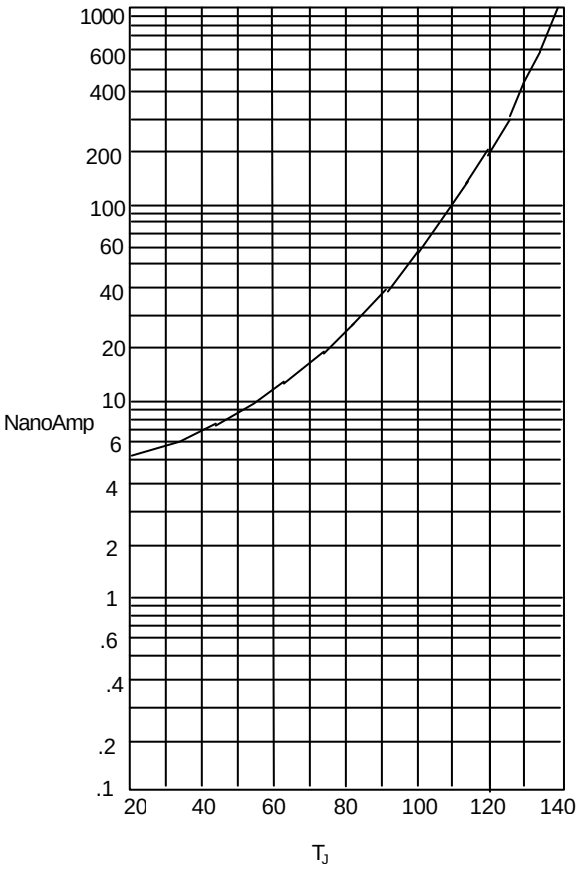
Admissable Power Dissipation - MilliWatts *versus*
Ambient Temperature -°C

Figure 3
Junction Capacitance



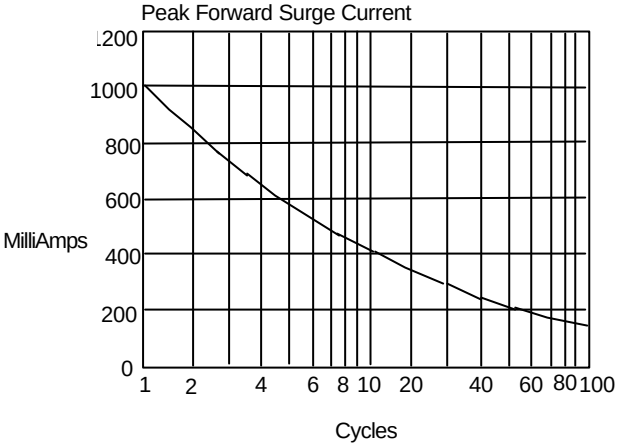
Junction Capacitance - pF *versus*
Reverse Voltage - Volts

Figure 4
Typical Reverse Characteristics



Instantaneous Reverse Leakage Current - NanoAmperes *versus* Junction Temperature - ^{O}C

Figure 5
Peak Forward Surge Current



Peak Forward Surge Current - Amperes *versus* Number Of Cycles At 60Hz - Cycles